PNP Silicon Epitaxial Planar Transistors
for switching, AF driver and amplifier applications.

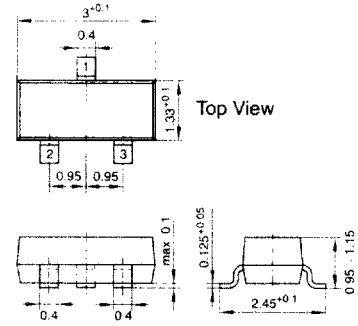
Especially suited for automatic insertion in thick- and thin-film circuits.

These transistors are subdivided into three groups -16, -25 and -40 according to their current gain.
As complementary types, the NPN transistors BC817 and BC818 are recommended.

Pin configuration
1 = Collector, 2 = Base, 3 = Emitter.

Marking code

Type	Marking
BC807-16	5A
-25	5B
-40	5C
BC808-16	5E
-25	5F
-40	5G



SOT-23 Plastic Package
Weight approx. 0.008 g
Dimensions in mm

Absolute Maximum Ratings

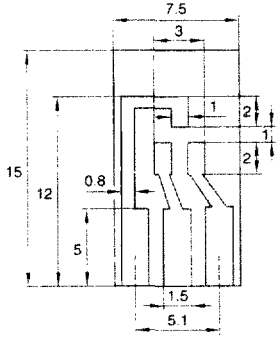
		Symbol	Value	Unit
Collector-Emitter Voltage	**BC807**	$-V_{CES}$	50	V
	BC808	$-V_{CES}$	30	V
Collector-Emitter Voltage	**BC807**	$-V_{CEO}$	45	V
	BC808	$-V_{CEO}$	25	V
Emitter-Base Voltage		$-V_{EBO}$	5	V
Collector Current		$-I_C$	500	mA
Peak Collector Current		$-I_{CM}$	1000	mA
Peak Base Current		$-I_{BM}$	200	mA
Peak Emitter Current		I_{EM}	1000	mA
Power Dissipation at T_{SB} = 50 °C		P_{tot}	310[1)]	mW
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_S	−65...+150	°C

[1)] Device on fiberglass substrate, see layout

Characteristics at T_{amb} = 25 °C

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE}$ = 1 V, $-I_C$ = 100 mA					
Current Gain Group-16	h_{FE}	100	–	250	–
-25	h_{FE}	160	–	400	–
-40	h_{FE}	250	–	600	–
at $-V_{CE}$ = 1 V, $-I_C$ = 300 mA **-16**	h_{FE}	60	–	–	–
-25	h_{FE}	100	–	–	–
-40	h_{FE}	170	–	–	–
Thermal Resistance Junction Substrate Backside	R_{thSB}	–	–	320[1]	K/W
Thermal Resistance Junction to Ambient Air	R_{thA}	–	–	450[1]	K/W
Collector Saturation Voltage at $-I_C$ = 500 mA, $-I_B$ = 50 mA	$-V_{CEsat}$	–	–	0.7	V
Base-Emitter Voltage at $-V_{CE}$ = 1 V, $-I_C$ = 300 mA	$-V_{BE}$	–	–	1.2	V
Collector-Emitter Cutoff Current					
at $-V_{CE}$ = 45 V **BC807**	$-I_{CES}$	–	–	100	nA
at $-V_{CE}$ = 25 V **BC808**	$-I_{CES}$	–	–	100	nA
at $-V_{CE}$ = 25 V, T_j = 150 °C	$-I_{CES}$	–	–	5	µA
Emitter-Base Cutoff Current at $-V_{EB}$ = 4 V	$-I_{EBO}$	–	–	100	nA
Gain-Bandwidth Product at $-V_{CE}$ = 5 V, $-I_C$ = 10 mA, f = 50 MHz	f_T	–	100	–	MHz
Collector-Base Capacitance at $-V_{CB}$ = 10 V, f = 1 MHz	C_{CBO}		12		pF

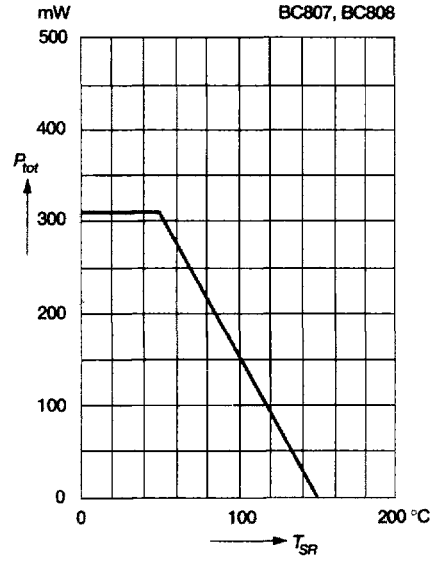
[1] Device on fiberglass substrate, see layout



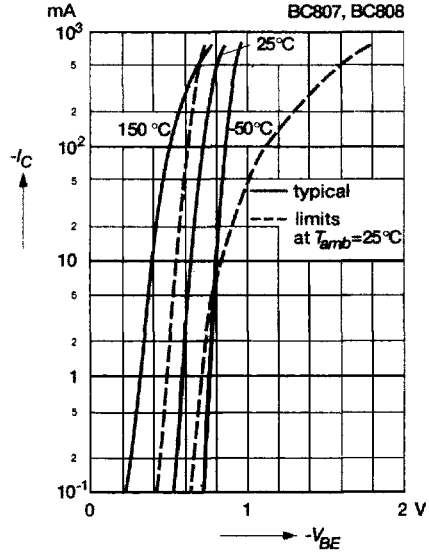
Layout for R_{thA} test
Thickness: Fiberglass 1.5 mm
Copper leads 0.3 mm

Admissible power dissipation versus temperature of substrate backside

Device on fiberglass substrate, see layout

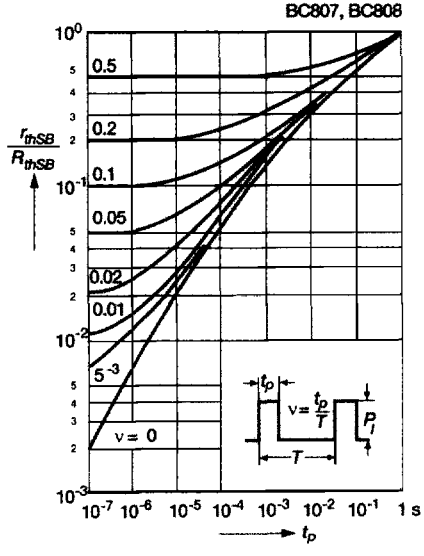


Collector current versus base-emitter voltage

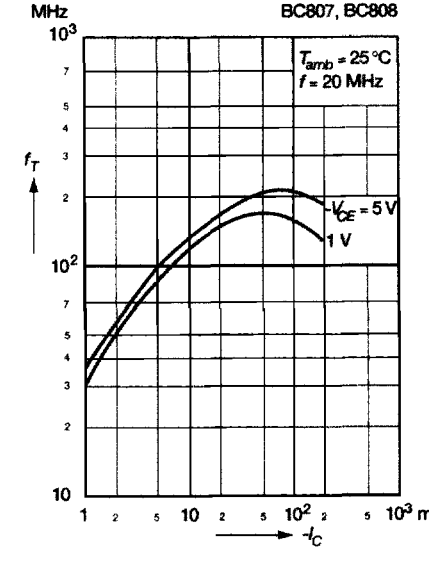


Pulse thermal resistance versus pulse duration (normalized)

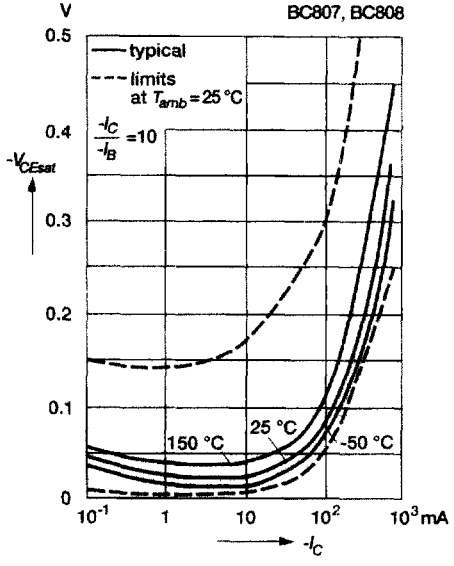
Device on fiberglass substrate, see layout



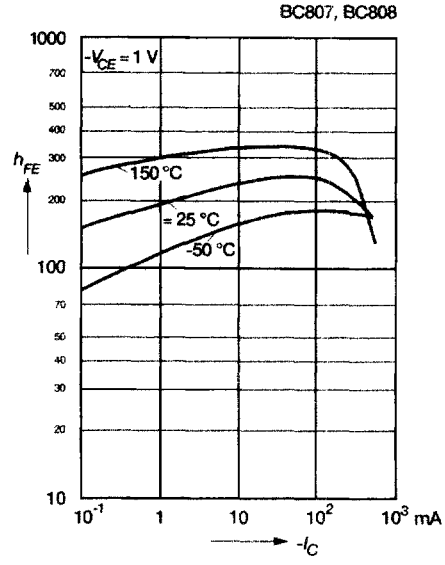
Gain-bandwidth product versus collector current



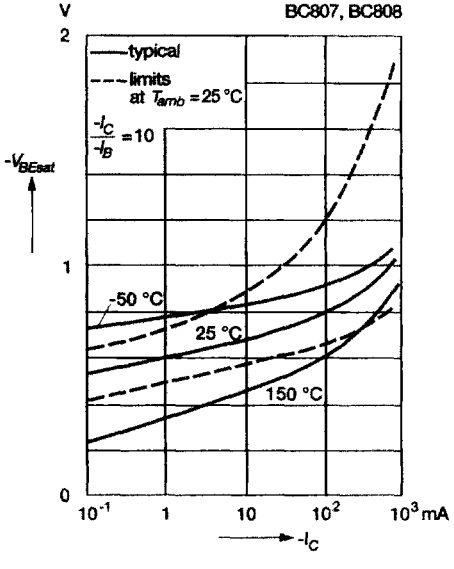
Collector saturation voltage versus collector current



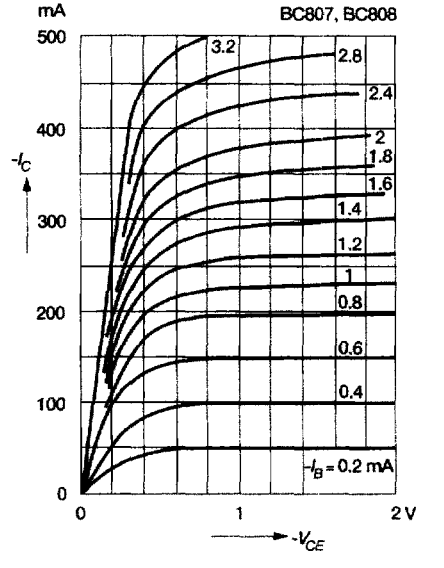
DC current gain versus collector current



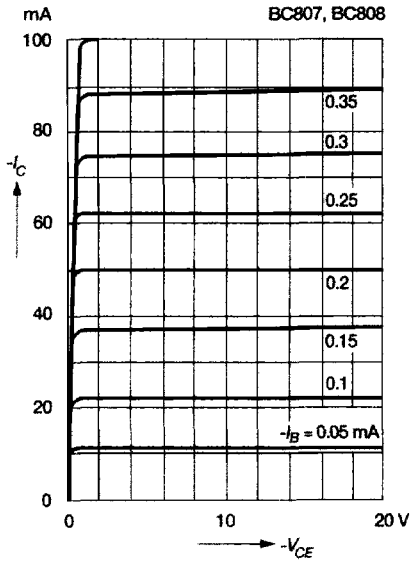
Base saturation voltage versus collector current



Common emitter collector characteristics



Common emitter collector characteristics



Common emitter collector characteristics